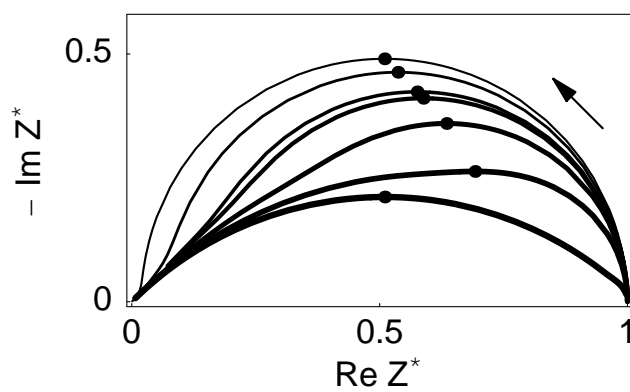


Handbook of Electrochemical Impedance Spectroscopy



DIFFUSION IMPEDANCES

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Chapter 1

Mass transfer by diffusion, Nernst boundary condition

1.1 General diffusion equations

From:

$$\frac{\partial \Delta c(x, t)}{\partial t} = D x^{1-d} \frac{\partial}{\partial x} \left(x^{d-1} \frac{\partial \Delta c(x, t)}{\partial x} \right)$$

where Δ denotes a small deviation (or excursion) from the initial steady-state value, $d = 1$ corresponds to a planar electrode, $d = 2$ to a cylindrical electrode (radial diffusion) and $d = 3$ to a spherical electrode [5, 32] (Fig. 1.1), it is obtained, using the Nernstian boundary condition $\Delta c(r_\delta) = 0$:

$$Z^*(u) \propto \frac{\Delta c(r_0, i u)}{\Delta J(r_0, i u)} = \frac{I_{d/2-1}(\sqrt{i u} \rho) K_{d/2-1}(\sqrt{i u}) - I_{d/2-1}(\sqrt{i u}) K_{d/2-1}(\sqrt{i u} \rho)}{\sqrt{i u} (I_{d/2}(\sqrt{i u}) K_{d/2-1}(\sqrt{i u} \rho) + I_{d/2-1}(\sqrt{i u} \rho) K_{d/2}(\sqrt{i u}))}$$

where u is a reduced frequency and $\rho = r_\delta/r_0$. $I_n(z)$ gives the modified Bessel function of the first kind and order n and $K_n(z)$ gives the modified Bessel function of the second kind and order n [47]. $I_n(z)$ and $K_n(z)$ satisfy the differential equation:

$$-y (n^2 + z^2) + z y' + z^2 y'' = 0$$

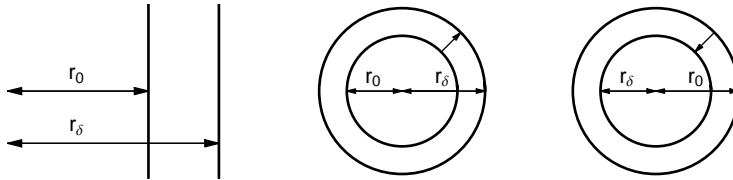


Figure 1.1: Planar diffusion (left), outside [18] (or convex [28]) diffusion ($\rho = r_\delta/r_0 > 1$, middle), and central (or concave) diffusion ($\rho < 1$, right).

1.2 Semi-infinite diffusion

1.2.1 Semi-infinite linear diffusion

$$d = 1, \Delta c(\infty) = 0$$

Impedance [43, 4]



Figure 1.2: Warburg element [46].

$$Z_W(\omega) = \frac{(1-i)\sigma}{\sqrt{\omega}} = \frac{\sqrt{2}\sigma}{\sqrt{i}\omega}, \quad \text{Re } Z_W(\omega) = \frac{\sigma}{\sqrt{\omega}}, \quad \text{Im } Z_W(\omega) = -\frac{\sigma}{\sqrt{\omega}}$$

$$\sigma = \frac{1}{n^2 F f X^* \sqrt{2 D_X}}, \quad f = \frac{F}{RT}, \quad X^* : \text{bulk concentration, } \sigma \text{ unit: } \Omega \text{ cm}^2 \text{ s}^{-1/2}$$

Reduced impedance

$$Z_W^*(u) = Z_W(\omega) = \frac{1}{\sqrt{i}u}, \quad u = \frac{\omega}{2\sigma^2}, \quad \text{Re } Z_W(u) = \frac{1}{\sqrt{2}u}, \quad \text{Im } Z_W(u) = -\frac{1}{\sqrt{2}u}$$

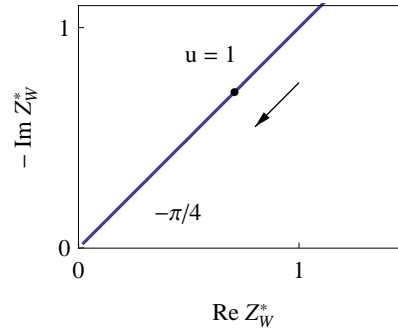


Figure 1.3: Nyquist diagram of the reduced Warburg impedance.

Randles circuit

The equivalent circuit in Fig. 1.4 was initially proposed by Randles for a redox reaction $O + ne \leftrightarrow R$ [37].

$$\sigma = \sigma_O + \sigma_R$$

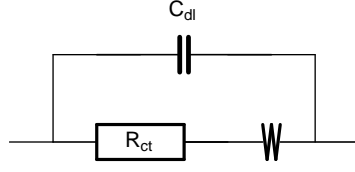


Figure 1.4: Randles circuit for semi-infinite linear diffusion.

Impedance

$$Z(\omega) = \frac{1}{i\omega C_{dl} + \frac{1}{R_{ct} + \frac{(1-i)\sigma}{\sqrt{\omega}}}} = \frac{-i((1-i)\sigma + \sqrt{\omega}R_{ct})}{-i\sqrt{\omega} + (1-i)\sigma\omega C_{dl} + \omega^{\frac{3}{2}}C_{dl}R_{ct}}$$

$$\text{Re } Z(\omega) = \frac{\sigma + \sqrt{\omega}R_{ct}}{\sqrt{\omega} \left(1 + 2\sigma\sqrt{\omega}C_{dl} + 2\sigma^2\omega C_{dl}^2 + 2\sigma\omega^{\frac{3}{2}}C_{dl}^2R_{ct} + \omega^2C_{dl}^2R_{ct}^2\right)}$$

$$\text{Im } Z(\omega) = \frac{-\sigma - 2\sigma^2\sqrt{\omega}C_{dl} - 2\sigma\omega C_{dl}R_{ct} - \omega^{\frac{3}{2}}C_{dl}R_{ct}^2}{\sqrt{\omega} \left(1 + 2\sigma\sqrt{\omega}C_{dl} + 2\sigma^2\omega C_{dl}^2 + 2\sigma\omega^{\frac{3}{2}}C_{dl}^2R_{ct} + \omega^2C_{dl}^2R_{ct}^2\right)}$$

Reduced impedance "The frequency response of the Randles circuit can be described in terms of two time constants for faradaic (τ_f) and diffusional (τ_d) processes" [45] (Fig. 1.5).

$$Z^*(u) = \frac{Z(u)}{R_{ct}} = \frac{(1+i)T(i+u)}{-T\sqrt{2u} + (1+i)(-1+T+iu)u}$$

$$u = \tau_d\omega, \tau_d = R_{ct}^2/(2\sigma^2), T = \tau_d/\tau_f, \tau_f = R_{ct}C_{dl}$$

$$\text{Re } Z^*(u) = \frac{T^2 \left(-(\sqrt{2}(-1+u)) + 2u^{\frac{3}{2}} \right)}{2\sqrt{2}Tu(1-T+u) + 2\sqrt{u} \left(T^2 + (-1+T)^2u + u^3 \right)}$$

$$\text{Im } Z^*(u) = \frac{T \left(\sqrt{2}T(-1-u) - 2\sqrt{u}(1-T+u^2) \right)}{2\sqrt{2}Tu(1-T+u) + 2\sqrt{u} \left(T^2 + (-1+T)^2u + u^3 \right)}$$

$$\lim_{u \rightarrow 0} \text{Re } Z^*(u) = 1 - \frac{1}{T} + \frac{1}{\sqrt{2}u}, \quad \lim_{u \rightarrow 0} \text{Im } Z^*(u) = -\frac{1}{\sqrt{2}u}$$

1.2.2 Semi-infinite radial cylindrical diffusion (outside)

$$d = 2, \Delta c(\infty) = 0$$

$$Z^*(u) = \frac{K_0(\sqrt{iu})}{\sqrt{iu}K_1(\sqrt{iu})}$$

$$\lim_{u \rightarrow 0} -\text{Im } Z^*(u) = \frac{\pi}{4}, \quad \text{Re } Z^*(u_c) = \frac{\pi}{4} \Rightarrow u_c = 0.542$$

(Fig. 1.6)

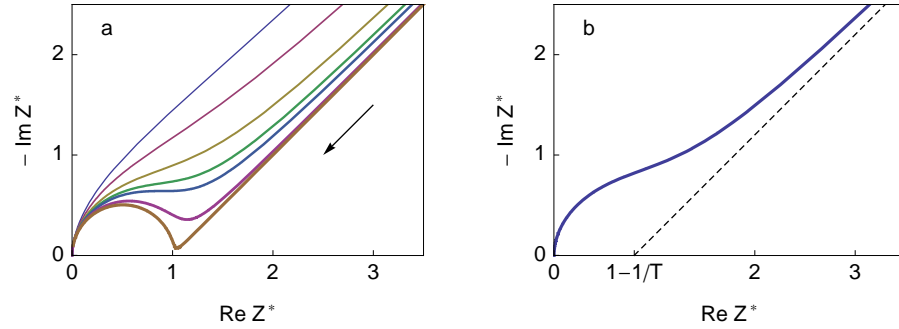


Figure 1.5: a: Nyquist diagram of the reduced impedance for the Randles circuit (Fig. 1.4). Semi-infinite linear diffusion. $T = 1, 2, 5, 10, 16.4822, 10^2, 10^4$. Line thickness increases with T . One apex for $T > 16.4822$. The arrows always indicate the increasing frequency direction. b: Extrapolation of the low frequency limit plotted for $T = 5$.

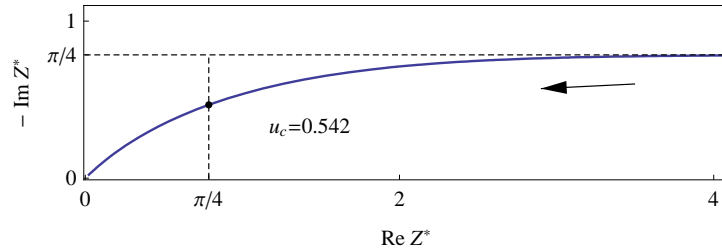


Figure 1.6: Reduced impedance for semi-infinite radial diffusion outside a circular cylinder. Dot: reduced characteristic angular frequency: $u_c = 0.542$.

1.2.3 Semi-infinite spherical diffusion

$$d = 3, \Delta c(\infty) = 0$$

$$Z^*(u) = \frac{1}{1 + \sqrt{i}u}, \quad u = r_0^2 \omega / D$$

$$\operatorname{Re} Z^*(u) = \frac{2 + \sqrt{2}u}{2(1 + \sqrt{2}u + u)}, \quad \operatorname{Im} Z^*(u) = -\frac{\sqrt{u}}{\sqrt{2}(1 + \sqrt{2}u + u)}$$

(Fig. 1.7)

1.3 Bounded diffusion condition (linear diffusion)

$$\Delta c(r_\delta) = 0$$

”Originally derived by Llopis and Colon [25], and subsequently re-derived by Sluyters [41] and Yzermans [49], Drossbach and Schultz [14], and Schuhmann [40]” [4].

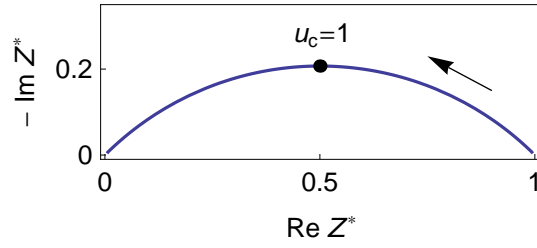


Figure 1.7: Reduced impedance for spherical (outside) diffusion. Dot: reduced characteristic angular frequency: $u_c = 1$, $\text{Re } Z^*(u_c) = 1/2$, $\text{Im } Z^*(u_c) = (1 - \sqrt{2})/2$.

- IUPAC terminology: bounded diffusion [42]
- Finite-length diffusion with transmissive boundary condition [21, 27]

$$Z_{W_\delta}^*(u) = \frac{\tanh \sqrt{i}u}{\sqrt{i}u}, \quad u = \tau_d \omega, \quad \tau_d = \delta^2/D, \quad \gamma = \sqrt{2}u$$

$$\lim_{u \rightarrow 0} Z_{W_\delta}^*(u) = 1, \quad \lim_{u \rightarrow \infty} \sqrt{i}u Z_{W_\delta}^*(u) = 1$$

$$\text{Re } Z_{W_\delta}^*(\gamma) = \frac{\sin(\gamma) + \sinh(\gamma)}{\gamma (\cos(\gamma) + \cosh(\gamma))}, \quad \text{Im } Z_{W_\delta}^*(\gamma) = \frac{\sin(\gamma) - \sinh(\gamma)}{\gamma (\cos(\gamma) + \cosh(\gamma))}$$

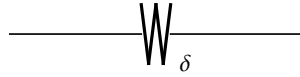


Figure 1.8: Bounded diffusion impedance.

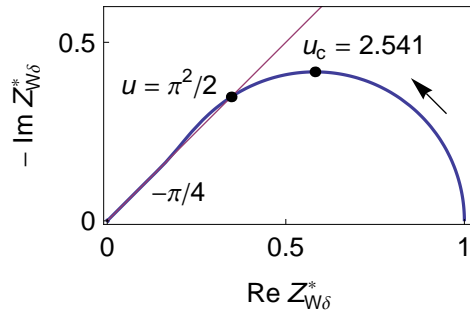


Figure 1.9: Nyquist diagram of the reduced bounded diffusion impedance. ($u = \pi^2/2$ [39]).

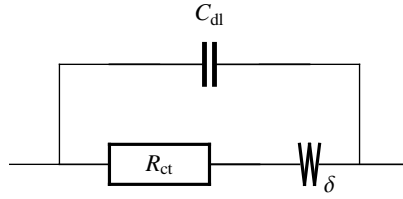


Figure 1.10: Randles circuit for bounded diffusion.

1.3.1 Randles circuit

Impedance

$$Z_f(u) = R_{ct} + R_d \frac{\tanh \sqrt{i u}}{\sqrt{i u}}, \quad u = \tau_d \omega, \quad \tau_d = \delta^2/D$$

$$\operatorname{Re} Z_f(\gamma) = R_{ct} + R_d \frac{\sin(\gamma) + \sinh(\gamma)}{\gamma (\cos(\gamma) + \cosh(\gamma))}, \quad \gamma = \sqrt{2 u}$$

$$\operatorname{Im} Z_f(\gamma) = R_d \frac{\sin(\gamma) - \sinh(\gamma)}{\gamma (\cos(\gamma) + \cosh(\gamma))}$$

$$Z(u) = \frac{Z_f(u)}{1 + i(u/\tau_d) C_{dl} Z_f(u)} = \frac{R_{ct} + R_d \frac{\tanh \sqrt{i u}}{\sqrt{i u}}}{1 + i(u/\tau_d) C_{dl} \left(R_{ct} + R_d \frac{\tanh \sqrt{i u}}{\sqrt{i u}} \right)}$$

Reduced impedance

(Fig. 1.11)

$$Z^*(u) = \frac{Z(u)}{R_{ct} + R_d} = \frac{1 + \frac{\tanh \sqrt{i u}}{\rho \sqrt{i u}}}{\left(1 + \frac{1}{\rho}\right) \left(1 + i u T + i u \frac{T}{\rho} \frac{\tanh \sqrt{i u}}{\rho \sqrt{i u}}\right)}$$

$$\rho = R_{ct}/R_d, \quad T = \tau_f/\tau_d, \quad \tau_f = R_{ct} C_{dl}$$

1.3.2 Corrosion equivalent circuit

Corrosion of a metal M with limitation by mass transport of oxidant (Fig. 1.12) on a rotating disk electrode (RDE) [33].

$$Z(u) = \frac{R_{ct} R_d \frac{\tanh \sqrt{i u}}{\sqrt{i u}}}{R_{ct} + R_d \frac{\tanh \sqrt{i u}}{\sqrt{i u}}}, \quad u = \tau_d \omega, \quad \tau_d = \delta^2/D \quad (1.1)$$

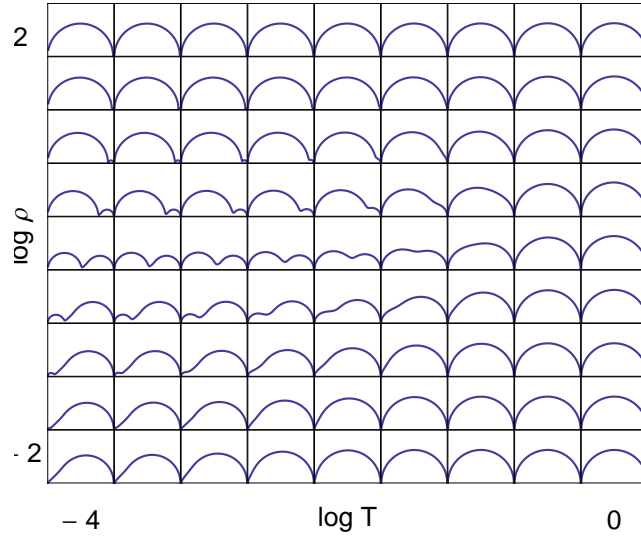


Figure 1.11: Impedance diagram array for the Randles circuit with bounded diffusion (Fig. 1.10).

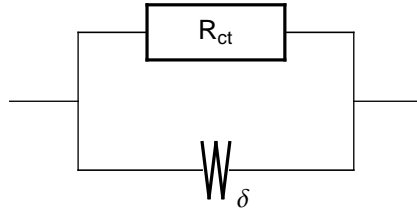


Figure 1.12: Equivalent circuit for corrosion of a metal M with limitation by mass transport of oxidant. R_{ct} : charge transfer of the reaction of metal oxidation.

$$Z^*(u) = (1 + \alpha) \frac{Z(u)}{R_d} = (1 + \alpha) \frac{\frac{\tanh \sqrt{i}u}{\sqrt{i}u}}{1 + \alpha \frac{\tanh \sqrt{i}u}{\sqrt{i}u}}, \quad \alpha = \frac{R_d}{R_{ct}} \quad (1.2)$$

Two limiting cases (Fig. 1.13):

- $\alpha \ll 1$:

$$Z^*(u) \approx \frac{\tanh \sqrt{i}u}{\sqrt{i}u}, \quad u_{c1} = 2.541, \quad \text{quarter of lemniscate, (Fig. 1.8)} \quad (1.3)$$

- $\alpha \gg 1$:

$$Z^*(u) \approx \frac{\alpha}{\alpha + \sqrt{i}u}, \quad u_{c2} = \alpha^2, \quad \text{quarter of circle, (Fig. 1.7)} \quad (1.4)$$

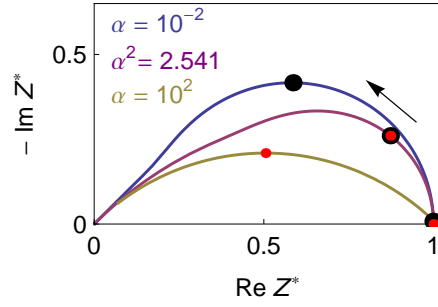


Figure 1.13: Nyquist diagram of the corrosion equivalent circuit. Large black dot : $u_{c1} = 2.541$, small red dot : $u_{c2} = \alpha^2$.

1.4 Analytical approximation

1.4.1 Analytical approximation #1

[12], Fig. 1.14.

$$Z^*(u) = \frac{\sqrt{\gamma + iu}}{\sqrt{\gamma}(1 + iu)}, \quad \gamma = 1.877 \quad (1.5)$$

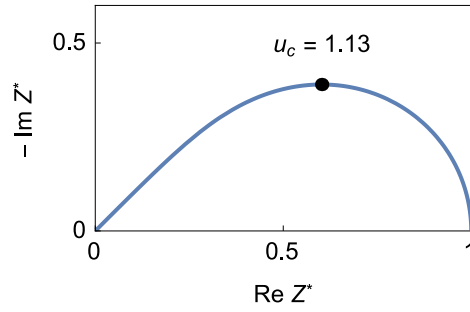


Figure 1.14: Nyquist diagram of the analytical approximation #1 (Eq. (1.5)).

1.4.2 Analytical approximation #2

[29], Fig. 1.15.

$$Z^*(f) = \frac{Z(f)}{R_d} = \frac{\sqrt{\gamma^2 + \tau_d i 2\pi f}}{\gamma + \tau_d i 2\pi f}, \quad \tau_d = \frac{\delta_d^2}{D} \quad (1.6)$$

where γ and τ_d depend on the Schmidt number Sc . For $Sc \in [10^2, 10^5]$:

$$\gamma = \frac{1.9930 - 1.6319 Sc^{-1/3}}{1 - 0.7248 Sc^{-1/3}} \quad (1.7)$$

$$\tau_d = \frac{1.61173^2}{\Omega} Sc^{1/3} (1 + 0.2980 Sc^{-1/3} + 0.14514 Sc^{-2/3} + 0.07020 Sc^{-1})^2 \quad (1.8)$$

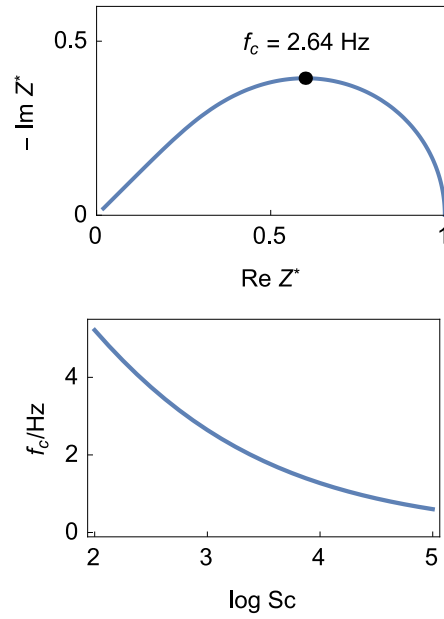


Figure 1.15: Nyquist diagram of the analytical approximation #2 (Eqs. (1.6)-(1.8), $Sc = 10^3$, $\Omega = 2000 \text{ tr min}^{-1}$) and change of f_c with Sc .

1.5 Radial cylindrical diffusion

$d = 2$ [18] (Fig. 1.1)

1.5.1 Finite-length diffusion outside a cylinder

$$Z^*(u) = \frac{I_0(\sqrt{i}u\rho)K_0(\sqrt{i}u) - I_0(\sqrt{i}u)K_0(\sqrt{i}u\rho)}{\text{Log}(\rho)\sqrt{i}u \left(I_1(\sqrt{i}u)K_0(\sqrt{i}u\rho) + I_0(\sqrt{i}u\rho)K_1(\sqrt{i}u) \right)}$$

$$u = r_0^2\omega/D, \quad \rho = r_s/r_0$$

Fig. 1.16 rectifies erroneous Figs. 7 and 8 in [30].

1.5.2 Semi-infinite outside a cylinder

$$\lim_{\rho \rightarrow \infty} Z^*(u) = \frac{K_0(\sqrt{i}u)}{\sqrt{i}u K_1(\sqrt{i}u)}$$

(Fig. 1.6)

1.6 Spherical diffusion

$d = 3$ [18] (Fig. 1.1)

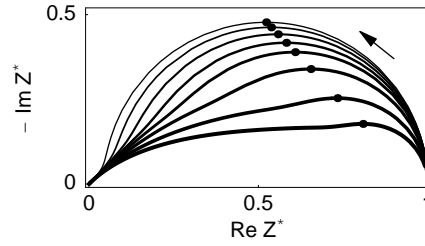


Figure 1.16: Central ($\rho < 1$) and outside ($\rho > 1$) cylindrical diffusion impedance. $\rho = r_\delta/r_0 = 10^{-2}, 10^{-1}, 0.4, 1.01, 2, 5, 20, 100$. The thickness increases with ρ . Dots: reduced characteristic angular frequency (apex of the impedance arc): $u_c = 0.514484, 1.22194, 4.74992, 25516., 3.40142, 0.298271, 0.0186746, 0.000800438$.

1.6.1 Finite-length diffusion outside a sphere, reduced impedance # 1

(Fig. 1.17)

$$Z^*(u) = \frac{1}{(1 - 1/\rho) \left(1 + \sqrt{i u} \coth(\sqrt{i u} (-1 + \rho))\right)}, \quad u = r_0^2 \omega / D, \quad \rho = r_\delta / r_0$$

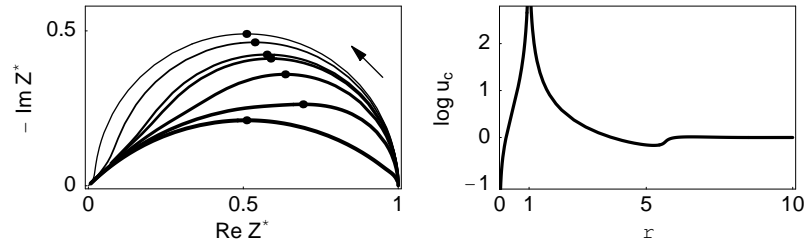


Figure 1.17: Central ($\rho < 1$) and outside ($\rho > 1$) spherical diffusion impedance. $\rho = r_\delta/r_0 = 0.1, 0.4, 0.91, 1.1, 2, 5, 50$. Line thickness increases with ρ . Dots: reduced characteristic angular frequency: $u_c = r_0^2 \omega / D = 0.3632, 3.095, 289, 275.8, 4.547, 0.6927, 1$. Change of $\log u_c$ with ρ .

1.6.2 Finite outside sphere, reduced impedance # 2

(Fig. 1.18)

$$Z^*(u) = \frac{1 + \delta}{\delta + \sqrt{i u} \coth(\sqrt{i u})}, \quad u = (r_\delta - r_0)^2 \omega / D, \quad \delta = (r_\delta - r_0) / r_0$$

1.6.3 Infinite outside sphere

(Fig. 1.7)

$$\lim_{\rho \rightarrow \infty} Z^*(u) = \frac{1}{1 + \sqrt{i u}}, \quad u = r_0^2 \omega / D$$

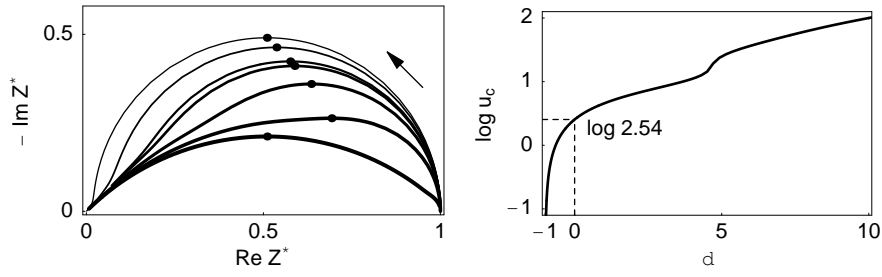


Figure 1.18: Central ($\delta < 0$) and outside ($\delta > 0$) spherical diffusion impedance. $\delta = (r_\delta - r_0)/r_0 = -0.99, -0.8, -0.5, -0.1, 0.1, 1, 3, 100$. Line thickness increases with δ . Dots: reduced characteristic angular frequency: $u_c = (r_\delta - r_0)^2 \omega / D = 0.0299, 0.577, 1.37, 2.32, 2.76, 4.55, 8.33, 10^4$, u_c increases with δ . Change of $\log u_c$ with δ .

$$\text{Re } Z^*(u) = \frac{2 + \sqrt{2u}}{2(1 + \sqrt{2u})}, \quad \text{Im } Z^*(u) = -\frac{\sqrt{u}}{\sqrt{2}(1 + \sqrt{2u} + u)}$$

Chapter 2

Mass transfer by diffusion, restricted diffusion

2.1 General diffusion equations

From:

$$\frac{\partial \Delta c(x,t)}{\partial t} = D x^{1-d} \frac{\partial}{\partial x} \left(x^{d-1} \frac{\partial \Delta c(x,t)}{\partial x} \right)$$

where Δ denotes a small deviation (or excursion) from the initial steady-state value, $d = 1$ corresponds to a planar electrode, $d = 2$ to a cylindrical electrode (radial diffusion) and $d = 3$ to a spherical electrode [5, 32] (Fig. 1.1), it is obtained, using the condition $\Delta J(r_\delta) = 0$:

$$Z^*(u) \propto \frac{\Delta c(r_0, i u)}{\Delta J(r_0, i u)} = \frac{I_{d/2-1}(\sqrt{i u}) K_{d/2}(\sqrt{i u} \rho) + I_{d/2}(\sqrt{i u} \rho) K_{d/2-1}(\sqrt{i u})}{\sqrt{i u} (I_{d/2}(\sqrt{i u} \rho) K_{d/2}(\sqrt{i u}) - I_{d/2}(\sqrt{i u}) K_{d/2}(\sqrt{i u} \rho))}$$

Terminology [31]: bounded system [19], finite-space diffusion [1, 2], finite length diffusion [22], restricted diffusion [10, 9, 13], reflective boundary condition [35], impermeable boundary [48], impermeable barrier condition [18], impermeable surface [11].



Figure 2.1: Restricted diffusion impedance. $d = 1$: thin planar layer, $d = 2$: cylinder, $d = 3$: sphere.

Internal cylinder and sphere with null radius, $r_0 = 0$.

$$Z^*(u) = \frac{I_{d/2-1}(\sqrt{i u})}{\sqrt{i u} I_{d/2}(\sqrt{i u})}$$

Fig. 2.2.

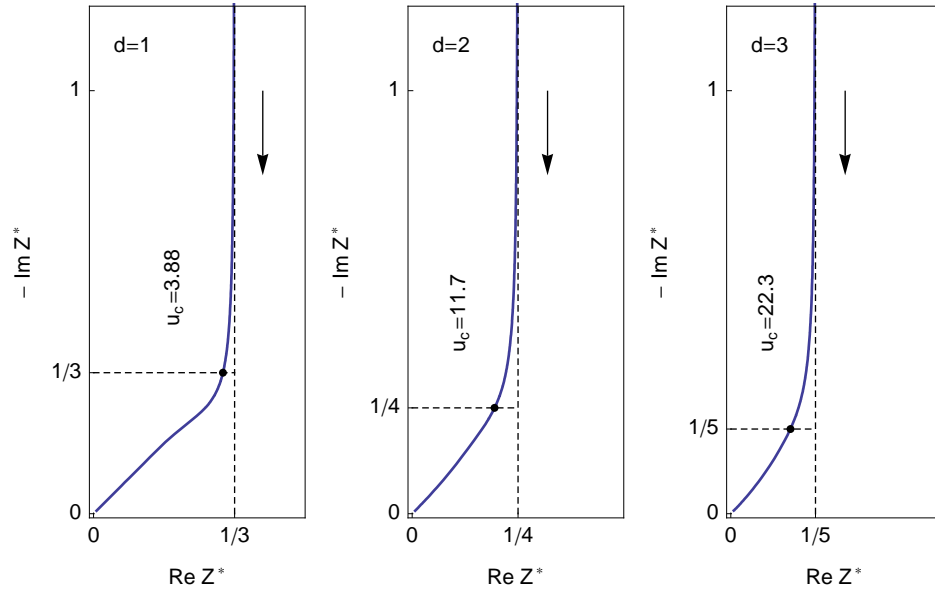


Figure 2.2: Nyquist diagram of the reduced impedance for the restricted diffusion impedance $Z^*(u)$ plotted for $d = 1, 2, 3$. $d = 1$: thin planar layer, $d = 2$: cylinder, $d = 3$: sphere. Dots: reduced characteristic angular frequency: $u_{c1} = 3.88$, $u_{c2} = 11.7$, $u_{c3} = 22.3$.

Low frequency limit

Fig. 2.3.

$$u \rightarrow 0 \Rightarrow Z^*(u) \approx \frac{1}{d+2} - \frac{id}{u}$$

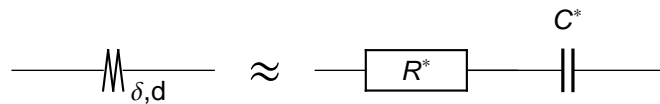


Figure 2.3: Low frequency equivalent circuit for restricted diffusion impedance. $R^* = 1/(d+2)$, $C^* = 1/d$.

High frequency limit

Fig. 2.4.

$$u \rightarrow \infty \Rightarrow Z^*(u) \approx \frac{1}{\sqrt{iu}}, \quad \lim_{u \rightarrow \infty} \sqrt{iu} Z^*(u) = 1$$



Figure 2.4: High frequency equivalent circuit for restricted diffusion impedance.

2.2 Linear diffusion and modified linear diffusion

2.2.1 Linear diffusion

$d = 1$

$$Z^*(u) = \frac{I_{d/2-1}(\sqrt{i}u)}{\sqrt{i}u I_{d/2}(\sqrt{i}u)} = \frac{I_{-1/2}(\sqrt{i}u)}{\sqrt{i}u I_{1/2}(\sqrt{i}u)} = \frac{\coth \sqrt{i}u}{\sqrt{i}u}$$

Reduced characteristic angular frequency: $u_{c1} \approx 3(d(d+2))$ [5], 5.12 [3], 4 [8], 3.88 [7].

$$\lim_{u \rightarrow 0} Z^*(u) = \frac{1}{3} + \frac{1}{i u}, \quad \lim_{u \rightarrow \infty} \sqrt{i}u Z^*(u) = 1$$

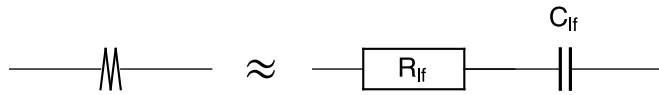
$$u = \tau_d \omega, \quad \tau_d = \delta^2/D, \quad \gamma = \sqrt{2}u$$

$$\operatorname{Re} Z^*(\gamma) = \frac{\sin(\gamma) - \sinh(\gamma)}{\gamma (\cos(\gamma) - \cosh(\gamma))}; \quad \operatorname{Im} Z^*(\gamma) = \frac{\sin(\gamma) + \sinh(\gamma)}{\gamma (\cos(\gamma) - \cosh(\gamma))}$$

Low frequency limit

Equivalent circuit: Fig. 2.5 ⁽¹⁾.

$$Z^*(u) = \frac{Z(u)}{R_d} \Rightarrow \lim_{\omega \rightarrow 0} Z(\omega) = \frac{R_d}{3} + \frac{R_d}{\tau_d i \omega} = R_{lf} + \frac{1}{C_{lf} i \omega}, \quad R_{lf} = \frac{R_d}{3}, \quad C_{lf} = \frac{\tau_d}{R_d}$$

Figure 2.5: Low frequency equivalent circuit for restricted diffusion impedance. $R_{lf} = R_d/3$, $C_{lf} = \tau_d/R_d$.

Randles circuit for restricted linear diffusion

Impedance

$$Z_f(u) = R_{ct} + R_d \frac{\coth \sqrt{i}u}{\sqrt{i}u}, \quad Z(u) = \frac{Z_f(u)}{1 + i(u/\tau_d) C_{dl} Z_f(u)}, \quad u = \tau_d \omega, \quad \tau_d = \delta^2/D$$

¹ For unit problems, don't forget the Farad unit : $F = s/\Omega$.

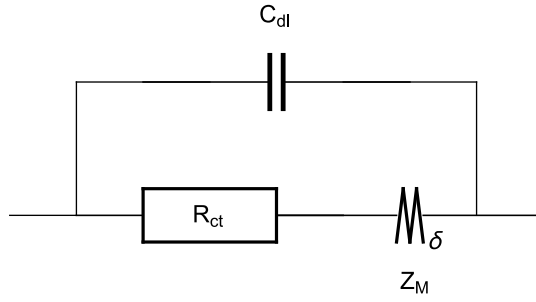
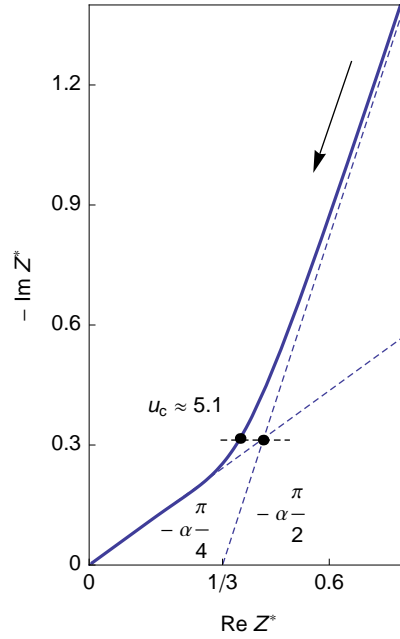


Figure 2.6: Randles circuit for restricted diffusion.

2.2.2 Modified restricted diffusion impedance

$\sqrt{i u}$ replaced by $(i u)^{\frac{\alpha}{2}}$ (α : dispersion parameter) [8, 7, 38], Fig. 2.7.


 Figure 2.7: Nyquist diagram of the reduced modified restricted diffusion impedance, plotted for $\alpha = 0.8$. u_c depends on α [7].

$$Z^*(u) = \frac{\coth(i u)^{\frac{\alpha}{2}}}{(i u)^{\frac{\alpha}{2}}}, \quad u = \tau_d \omega, \quad \tau_d = \delta^2 / D$$

$$\text{Re } Z^*(u) = \frac{u^{-\alpha/2} (\sin(\frac{\pi\alpha}{4}) \sin(2u^{\alpha/2} \sin(\frac{\pi\alpha}{4})) - \cos(\frac{\pi\alpha}{4}) \sinh(2u^{\alpha/2} \cos(\frac{\pi\alpha}{4})))}{\cos(2u^{\alpha/2} \sin(\frac{\pi\alpha}{4})) - \cosh(2u^{\alpha/2} \cos(\frac{\pi\alpha}{4}))}$$

$$\text{Im } Z^*(u) = \frac{u^{-\alpha/2} (\cos(\frac{\pi\alpha}{4}) \sin(2u^{\alpha/2} \sin(\frac{\pi\alpha}{4})) + \sin(\frac{\pi\alpha}{4}) \sinh(2u^{\alpha/2} \cos(\frac{\pi\alpha}{4})))}{\cos(2u^{\alpha/2} \sin(\frac{\pi\alpha}{4})) - \cosh(2u^{\alpha/2} \cos(\frac{\pi\alpha}{4}))}$$

Low frequency limit

Equivalent circuit: Fig. 2.8.

$$u \rightarrow 0 \Rightarrow Z^*(u) \approx \frac{1}{3} + \frac{1}{(iu)^\alpha}$$

$$Z^*(u) = \frac{Z(u)}{R_d} \Rightarrow \lim_{\omega \rightarrow 0} Z(\omega) = \frac{R_d}{3} + \frac{R_d}{(i\tau_d \omega)^\alpha} = R_{lf} + \frac{1}{Q_{lf}(i\omega)^\alpha}, \quad R_{lf} = \frac{R_d}{3}, \quad Q_{lf} = \frac{\tau_d^\alpha}{R_d}$$

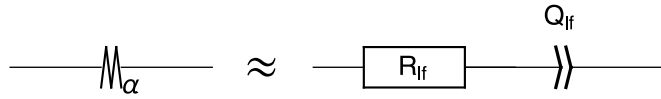


Figure 2.8: Low frequency equivalent circuit for modified restricted diffusion impedance. $R_{lf} = R_d/3$, $Q_{lf} = \tau_d^\alpha/R_d$. Q_{lf} unit : $\frac{s^\alpha}{\Omega} = \frac{s}{\Omega} \frac{s^\alpha}{s} = F s^{\alpha-1}$.

2.2.3 Anomalous diffusion impedance

[6], Fig. 2.9.

$$Z(\omega) = R_d \frac{\coth(i\omega \tau_d)^{\gamma/2}}{(i\omega \tau_d)^{1-\gamma/2}}, \quad \gamma \leq 1$$

$$Z(u)^* = \frac{Z(\omega)}{R_d} = \frac{\coth(iu)^{\gamma/2}}{(iu)^{1-\gamma/2}}, \quad u = \omega \tau_d, \tau_d = \left(\frac{\delta^2}{D}\right)^{1/\gamma}$$

The D unit ($D/\text{cm}^2 \text{ s}^{-\gamma}$) depends on γ .

$$\text{Re } Z^*(u) = \frac{u^{\frac{\gamma}{2}-1} \left(\cos\left(\frac{\pi\gamma}{4}\right) \sin\left(2u^{\gamma/2} \sin\left(\frac{\pi\gamma}{4}\right)\right) - \sin\left(\frac{\pi\gamma}{4}\right) \sinh\left(2u^{\gamma/2} \cos\left(\frac{\pi\gamma}{4}\right)\right) \right)}{\cos\left(2u^{\gamma/2} \sin\left(\frac{\pi\gamma}{4}\right)\right) - \cosh\left(2u^{\gamma/2} \cos\left(\frac{\pi\gamma}{4}\right)\right)}$$

$$\text{Im } Z^*(u) = \frac{u^{\frac{\gamma}{2}-1} \left(\sin\left(\frac{\pi\gamma}{4}\right) \sin\left(2u^{\gamma/2} \sin\left(\frac{\pi\gamma}{4}\right)\right) + \cos\left(\frac{\pi\gamma}{4}\right) \sinh\left(2u^{\gamma/2} \cos\left(\frac{\pi\gamma}{4}\right)\right) \right)}{\cos\left(2u^{\gamma/2} \sin\left(\frac{\pi\gamma}{4}\right)\right) - \cosh\left(2u^{\gamma/2} \cos\left(\frac{\pi\gamma}{4}\right)\right)}$$

2.3 Cylindrical diffusion

$d = 2$, δ : cylinder radius

$$Z^*(u) = \frac{I_{d/2-1}(\sqrt{i}u)}{\sqrt{i}u I_{d/2}(\sqrt{i}u)} = \frac{I_0(\sqrt{i}u)}{\sqrt{i}u I_1(\sqrt{i}u)}$$

$$\lim_{u \rightarrow 0} Z^*(u) = \frac{1}{4} - \frac{2i}{u}, \quad \lim_{u \rightarrow \infty} \sqrt{i}u Z^*(u) = 1$$

$$u = \tau_d \omega, \quad \tau_d = \delta^2/D$$

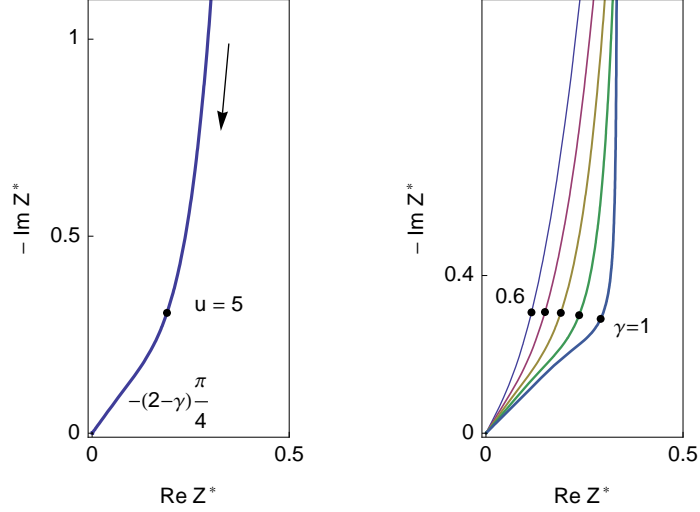


Figure 2.9: Nyquist diagram of the reduced anomalous diffusion impedance. Left: $\gamma = 0.8$, right: change of Nyquist diagram with γ ($\gamma : 1, 0.9, 0.8, 0.7, 0.6$). Dots: $u = 5$ [6].

Low frequency limit

Equivalent circuit: $R_{lf} + C_{lf}$.

$$Z^*(u) = \frac{Z(u)}{R_d} \Rightarrow \lim_{\omega \rightarrow 0} Z(\omega) = \frac{R_d}{4} + \frac{2R_d}{\tau_d i \omega} = R_{lf} + \frac{1}{C_{lf} i \omega}, \quad R_{lf} = \frac{R_d}{4}, \quad C_{lf} = \frac{\tau_d}{2R_d}$$

2.4 Spherical diffusion

$d = 3$, δ : sphere radius

$$Z^*(u) = \frac{I_{d/2-1}(\sqrt{i}u)}{\sqrt{i}u I_{d/2}(\sqrt{i}u)} = \frac{I_{1/2}(\sqrt{i}u)}{\sqrt{i}u I_{3/2}(\sqrt{i}u)} = \frac{1}{-1 + \sqrt{i}u \coth \sqrt{i}u}$$

$$\lim_{u \rightarrow 0} Z^*(u) = \frac{1}{5} - \frac{3i}{u}, \quad \lim_{u \rightarrow \infty} \sqrt{i}u Z^*(u) = 1$$

$$u = \tau_d \omega, \quad \tau_d = \delta^2/D, \quad \gamma = \sqrt{2}u$$

$$\operatorname{Re} Z^*(\gamma) = \frac{2 \cos(\gamma) - 2 \cosh(\gamma) + \gamma \sin(\gamma) + \gamma \sinh(\gamma)}{(-2 + \gamma^2) \cos(\gamma) + (2 + \gamma^2) \cosh(\gamma) - 2\gamma (\sin(\gamma) + \sinh(\gamma))}$$

$$\operatorname{Im} Z^*(\gamma) = \frac{\gamma (\sin(\gamma) - \sinh(\gamma))}{(-2 + \gamma^2) \cos(\gamma) + (2 + \gamma^2) \cosh(\gamma) - 2\gamma (\sin(\gamma) + \sinh(\gamma))}$$

Low frequency limit

Equivalent circuit: $R_{lf} + C_{lf}$.

$$Z^*(u) = \frac{Z(u)}{R_d} \Rightarrow \lim_{\omega \rightarrow 0} Z(\omega) = \frac{R_d}{5} + \frac{3R_d}{\tau_d i \omega} = R_{lf} + \frac{1}{C_{lf} i \omega}, \quad R_{lf} = \frac{R_d}{5}, \quad C_{lf} = \frac{\tau_d}{3R_d}$$

Chapter 3

Gerischer and diffusion-reaction impedance

3.1 Gerischer and modified Gerischer impedance

3.1.1 Gerischer impedance

$$Z_G^*(u) = \frac{1}{\sqrt{1+iu}} \quad (3.1)$$

"In view of the earliest derivation of such an impedance by Gerischer, [15] it seems a good idea to name it the "Gerischer impedance" Z_G " [42, 44].

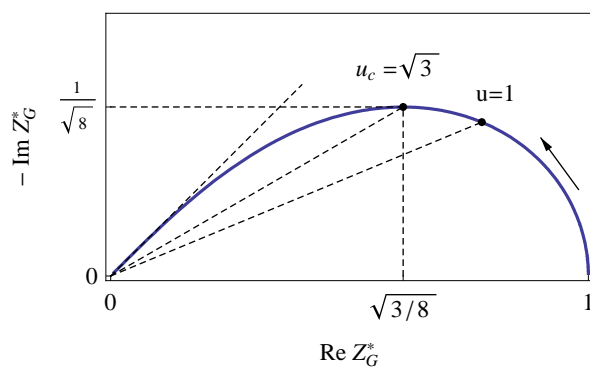


Figure 3.1: Reduced Gerischer impedance. Some characteristic values are given in [23, 24]. Phase angle for dashed lines : $-\pi/8$, $-\pi/6$ and $-\pi/4$ respectively.

$$\lim_{u \rightarrow 0} Z_G^*(u) = 1, \quad \lim_{u \rightarrow \infty} \sqrt{iu} Z_G^*(u) = 1$$

$$\operatorname{Re} Z_G^*(u) = \frac{\cos\left(\frac{\arctan(u)}{2}\right)}{(1+u^2)^{1/4}} = \frac{\sqrt{\sqrt{1+u^{-2}}+u^{-1}}}{\sqrt{2}\sqrt{1+u^{-2}}\sqrt{u}}$$

$$\operatorname{Im} Z_G^*(u) = -\frac{\sin\left(\frac{\arctan(u)}{2}\right)}{(1+u^2)^{1/4}} = -\frac{\sqrt{\sqrt{1+u^{-2}}-u^{-1}}}{\sqrt{2}\sqrt{1+u^{-2}}\sqrt{u}}$$

$$\frac{d\operatorname{Im} Z_G^*(u)}{du} = \frac{-2 + \sqrt{1+u^{-2}}u}{2\sqrt{2}\sqrt{1+u^{-2}}\sqrt{\sqrt{1+u^{-2}}-\frac{1}{u}}\sqrt{u}(1+u^2)} = 0 \Rightarrow u_c = \sqrt{3}$$

$$\text{Diagnostic criterion [16, 34] } \operatorname{Re} Y_G^*(u)^2 - \operatorname{Im} Y_G^*(u)^2 = 1$$

3.1.2 Modified Gerischer impedance #1

$$Z_{G\alpha}^*(u) = \frac{1}{\sqrt{1+(iu)^\alpha}}$$

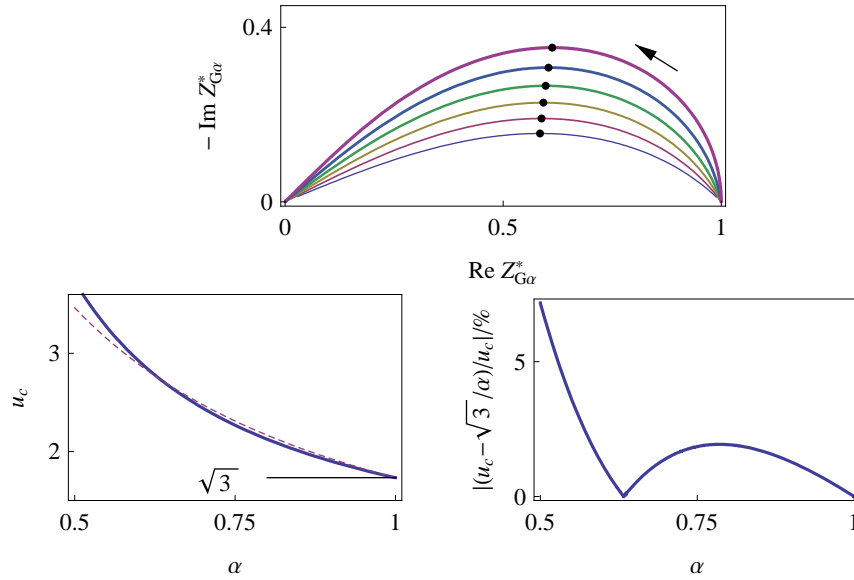


Figure 3.2: Reduced modified Gerischer impedance. $\alpha = 0.5, 0.6, 0.7, 0.8, 0.9, 1$. Line thickness increases with α . Dots: characteristic frequency u_c at the apex of the impedance arc. Change of u_c for the modified Gerischer impedance (solid line) and change of $\sqrt{3}/\alpha$ with α (dashed line). $u_c \approx \sqrt{3}/\alpha$ for $\alpha \in [0.53, 1]$ ($|(u_c - \sqrt{3}/\alpha)|/u_c < 5\%$).

$$\operatorname{Re} Z_{G\alpha}^*(u) = \frac{\cos\left(\frac{1}{2}\arctan\left(\frac{u^\alpha \sin\left(\frac{\pi\alpha}{2}\right)}{1 + u^\alpha \cos\left(\frac{\pi\alpha}{2}\right)}\right)\right)}{\left(1 + u^{2\alpha} + 2u^\alpha \cos\left(\frac{\pi\alpha}{2}\right)\right)^{\frac{1}{4}}}$$

$$\operatorname{Im} Z_{G\alpha}^*(u) = -\frac{\sin\left(\frac{1}{2}\arctan\left(\frac{u^\alpha \sin\left(\frac{\pi\alpha}{2}\right)}{1 + u^\alpha \cos\left(\frac{\pi\alpha}{2}\right)}\right)\right)}{\left(1 + u^{2\alpha} + 2u^\alpha \cos\left(\frac{\pi\alpha}{2}\right)\right)^{\frac{1}{4}}}$$

3.1.3 Modified Gerischer impedance #2

$$Z_{G\alpha 2}^*(u) = \frac{1}{(1 + iu)^{\alpha/2}}, \quad \alpha \in [0, 1]$$

$$\operatorname{Re} Z_{G\alpha 2}^*(u) = (u^2 + 1)^{-\alpha/4} \cos\left(\frac{1}{2}\alpha \arctan(u)\right)$$

$$\operatorname{Im} Z_{G\alpha 2}^*(u) = - (u^2 + 1)^{-\alpha/4} \sin\left(\frac{1}{2}\alpha \arctan(u)\right)$$

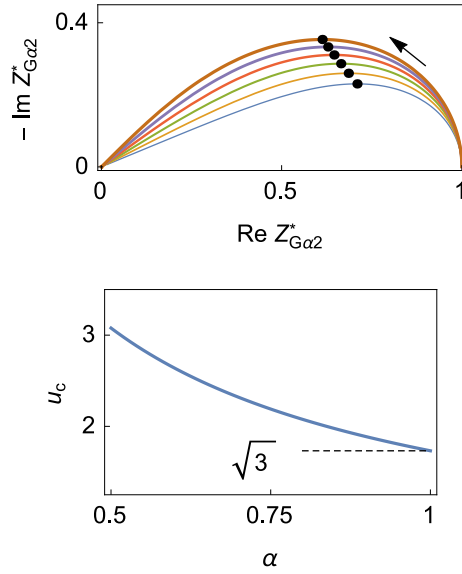


Figure 3.3: Reduced modified Gerischer impedance #2. $\alpha = 0.5, 0.6, 0.7, 0.8, 0.9, 1$ ($\alpha = 1$: Gerischer impedance Eq. (3.1)). Line thickness increases with α . Dots: characteristic frequency u_c at the apex of the impedance arc. Change of u_c for the modified Gerischer impedance #2.

3.1.4 Modified Gerischer impedance #3

[36, 26], Fig. 3.4.

$$Z_{G\alpha 3}^*(u) = \frac{1}{(1 + iu)^\alpha}, \quad \alpha \in [0, 1]$$

$$\operatorname{Re} Z_{G\alpha 3}^*(u) = (u^2 + 1)^{-\alpha/2} \cos(\alpha \arctan(u))$$

$$\operatorname{Im} Z_{G\alpha 3}^*(u) = - (u^2 + 1)^{-\alpha/2} \sin(\alpha \arctan(u))$$

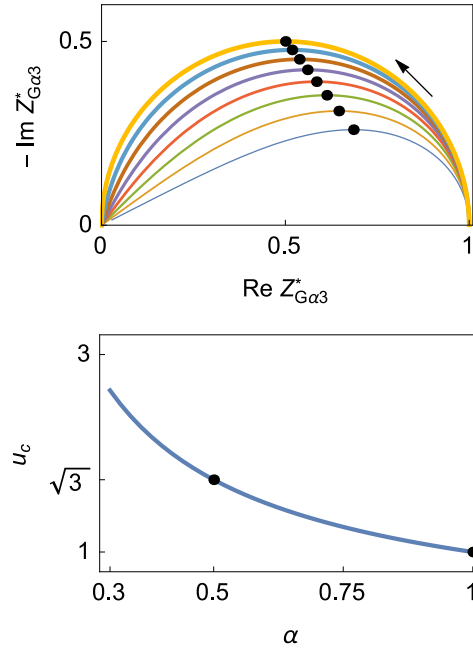


Figure 3.4: Reduced modified Gerischer impedance #3. $\alpha = 0.3, 0.4, 0.5, 0.6, 0.7, 0.8, 0.9, 1$ ($\alpha = 0.5$: Gerischer impedance Eq. (3.1)). Line thickness increases with α . Dots: characteristic frequency u_c at the apex of the impedance arc. Change of u_c for the modified Gerischer impedance #3.

3.1.5 Havriliak-Negami impedance

[17, 20], Fig. 3.5.

$$Z_{\text{HN}}^*(u) = \frac{1}{(1 + (iu)^\alpha)^\beta} \quad (3.2)$$

$$\text{Re } Z_{\text{HN}}^*(u) = \left(u^{2\alpha} + 2 \cos\left(\frac{\pi\alpha}{2}\right) u^\alpha + 1 \right)^{-\beta/2} \cos\left(\beta \arctan\left(\frac{\sin\left(\frac{\pi\alpha}{2}\right) u^\alpha}{\cos\left(\frac{\pi\alpha}{2}\right) u^\alpha + 1} \right) \right) \quad (3.3)$$

$$\text{Im } Z_{\text{HN}}^*(u) = - \left(u^{2\alpha} + 2 \cos\left(\frac{\pi\alpha}{2}\right) u^\alpha + 1 \right)^{-\beta/2} \sin\left(\beta \arctan\left(\frac{\sin\left(\frac{\pi\alpha}{2}\right) u^\alpha}{\cos\left(\frac{\pi\alpha}{2}\right) u^\alpha + 1} \right) \right) \quad (3.4)$$

- $\beta = 1/2 \Rightarrow$ modified Gerischer impedance #1 (cf. § 3.1.2, p. 26)
- $\alpha = 1 \Rightarrow$ modified Gerischer impedance #2, (cf. § 3.1.3, p. 27), #3, (cf. § 3.1.4, p. 27)

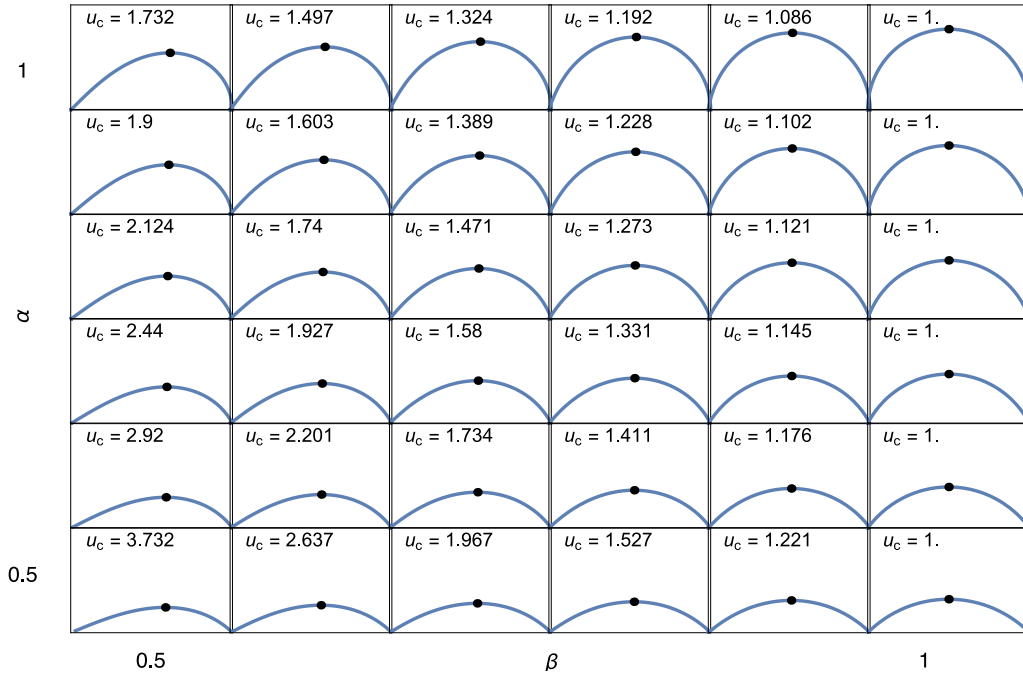


Figure 3.5: Impedance diagram array for the reduced Havriliak-Negami impedance. $u_c = \sqrt{3}$ ($\alpha = 1, \beta = 1/2$), $u_c = 2 + \sqrt{3}$ ($\alpha = \beta = 1/2$), $u_c = 1$ ($\beta = 1, \forall \alpha$).

3.2 Diffusion-reaction impedance

3.2.1 Reduced impedance #1

$$Z^*(u) = \frac{\sqrt{\lambda}}{\tanh \sqrt{\lambda}} \frac{\tanh \sqrt{i u + \lambda}}{\sqrt{i u + \lambda}}$$

$$\lim_{u \rightarrow 0} Z^*(u) = 1, \quad \lim_{u \rightarrow \infty} \sqrt{i u + \lambda} Z^*(u) = \sqrt{\lambda} \coth \sqrt{\lambda}$$

$$\lambda \rightarrow 0 \Rightarrow Z^*(u) \approx Z_{W\delta}^*(u) = \frac{\tanh \sqrt{i u}}{\sqrt{i u}}, \quad \lambda \rightarrow \infty \Rightarrow Z^*(u) \approx Z_G^*(u/\lambda) = \frac{1}{\sqrt{1 + i u/\lambda}}$$

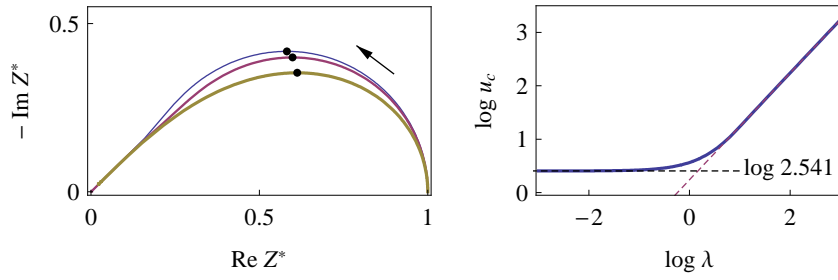


Figure 3.6: Diffusion-reaction reduced impedance #1. $\lambda = 10^{-3}, 1, 10^3$. Line thickness increases with λ . $u_c = 2.542, 3.657, 1732$. Change of $\log u_c$ with $\log \lambda$ for the diffusion-reaction reduced impedance #1. $\lambda \rightarrow 0 \Rightarrow u_c \rightarrow 2.54, \lambda \rightarrow \infty \Rightarrow u_c \approx \lambda\sqrt{3}$.

$$\operatorname{Re} Z^*(u) = \frac{\sqrt{\lambda} \coth(\sqrt{\lambda}) \left(\sinh(2(u^2 + \lambda^2)^{\frac{1}{4}} ca_{u\lambda}) ca_{u\lambda} + \sin(2(u^2 + \lambda^2)^{\frac{1}{4}} sa_{u\lambda}) sa_{u\lambda} \right)}{(u^2 + \lambda^2)^{\frac{1}{4}} \left(\cos(2(u^2 + \lambda^2)^{\frac{1}{4}} sa_{u\lambda}) + \cosh(2(u^2 + \lambda^2)^{\frac{1}{4}} ca_{u\lambda}) \right)}$$

$$ca_{u\lambda} = \cos\left(\frac{\arctan\left(\frac{u}{\lambda}\right)}{2}\right), \quad sa_{u\lambda} = \sin\left(\frac{\arctan\left(\frac{u}{\lambda}\right)}{2}\right)$$

$$\operatorname{Im} Z^*(u) = \frac{\sqrt{\lambda} \coth(\sqrt{\lambda}) \left(\sin(2(u^2 + \lambda^2)^{\frac{1}{4}} sa_{u\lambda}) ca_{u\lambda} - \sinh(2(u^2 + \lambda^2)^{\frac{1}{4}} ca_{u\lambda}) sa_{u\lambda} \right)}{(u^2 + \lambda^2)^{\frac{1}{4}} \left(\cos(2(u^2 + \lambda^2)^{\frac{1}{4}} sa_{u\lambda}) + \cosh(2(u^2 + \lambda^2)^{\frac{1}{4}} ca_{u\lambda}) \right)}$$

3.2.2 Reduced impedance #2

$$Z^*(u) = \frac{\sqrt{\lambda} \coth \sqrt{\lambda} \tanh \sqrt{(1 + i u) \lambda}}{\sqrt{(1 + i u) \lambda}}$$

$$\lim_{u \rightarrow 0} Z^*(u) = 1, \quad \lim_{u \rightarrow \infty} \sqrt{(1 + i u) \lambda} Z^*(u) = \sqrt{\lambda} \coth \sqrt{\lambda}$$

$$\lim_{\lambda \rightarrow 0} Z^*(u) = Z_{W\delta}(u/\lambda) = \frac{\tanh \sqrt{i u/\lambda}}{\sqrt{i u/\lambda}}, \quad \lim_{\lambda \rightarrow \infty} Z^*(u) = Z_G^*(u) = \frac{1}{\sqrt{1 + i u}}$$

$$\operatorname{Re} Z^*(u) = \frac{\coth(\sqrt{\lambda}) \left(\sinh(2(1 + u^2)^{\frac{1}{4}} \sqrt{\lambda} ca_u) ca_u + \sin(2(1 + u^2)^{\frac{1}{4}} \sqrt{\lambda} sa_u) sa_u \right)}{(1 + u^2)^{\frac{1}{4}} \left(\cos(2(1 + u^2)^{\frac{1}{4}} \sqrt{\lambda} sa_u) + \cosh(2(1 + u^2)^{\frac{1}{4}} \sqrt{\lambda} ca_u) \right)}$$

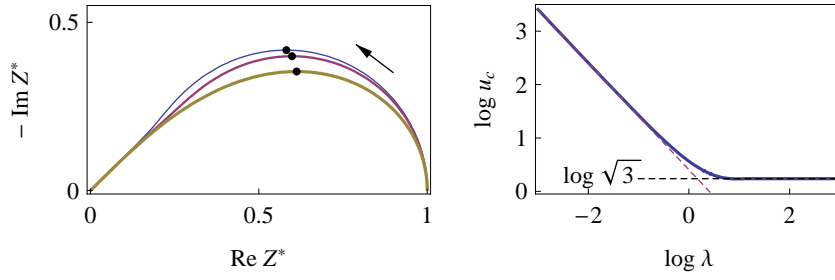


Figure 3.7: Diffusion-reaction reduced impedance #2. $\lambda = 10^{-4}, 1, 10^3$. Line thickness increases with λ . $u_c = 25407, 3.657, 1.732$. Change of $\log u_c$ with $\log \lambda$ for the diffusion-reaction reduced impedance #2. $\lambda \rightarrow 0 \Rightarrow u_c \approx 1/(2.54 \lambda)$, $\lambda \rightarrow \infty \Rightarrow u_c \rightarrow \sqrt{3}$.

$$ca_u = \cos\left(\frac{\arctan(u)}{2}\right), \quad sa_u = \sin\left(\frac{\arctan(u)}{2}\right)$$

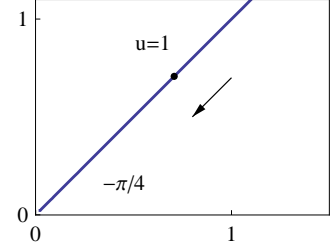
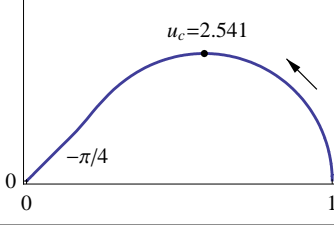
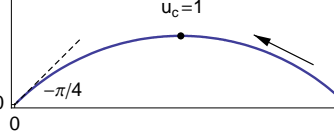
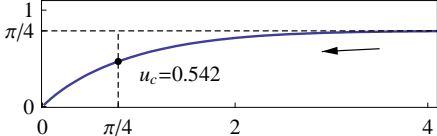
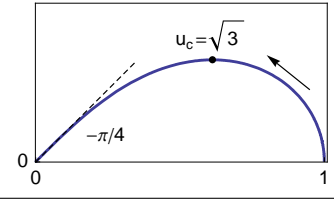
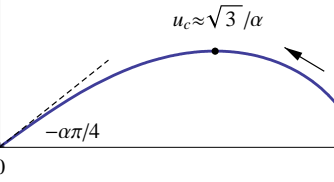
$$\text{Im } Z^*(u) = \frac{\coth(\sqrt{\lambda}) \left(\sin(2(1+u^2)^{\frac{1}{4}} \sqrt{\lambda} sa_u) ca_u - \sinh(2(1+u^2)^{\frac{1}{4}} \sqrt{\lambda} ca_u) sa_u \right)}{(1+u^2)^{\frac{1}{4}} \left(\cos(2(1+u^2)^{\frac{1}{4}} \sqrt{\lambda} sa_u) + \cosh(2(1+u^2)^{\frac{1}{4}} \sqrt{\lambda} ca_u) \right)}$$

Chapter 4

Appendix

4.1 Table bounded diffusion and diffusion-reaction impedance

Table 4.1: Bounded diffusion and diffusion-reaction impedance.

| Denomination | Reduced impedance | Nyquist impedance diagram |
|------------------------------|---|--|
| Warburg | $Z_W^* = \frac{1}{\sqrt{i}u}$ |  |
| Bounded diffusion | $Z_{W_\delta}^* = \frac{\tanh \sqrt{i}u}{\sqrt{i}u}$ |  |
| Semi-∞ spherical diffusion | $Z^* = \frac{1}{1 + \sqrt{i}u}$ |  |
| Semi-∞ cylindrical diffusion | $Z^* = \frac{K_0(\sqrt{i}u)}{\sqrt{i}u K_1(\sqrt{i}u)}$ |  |
| Gerischer | $Z_G^* = \frac{1}{\sqrt{1 + i}u}$ |  |
| Modified Gerischer | $Z_{G\alpha}^* = \frac{1}{\sqrt{1 + (i)u}^\alpha}$ |  |

4.2 Table restricted diffusion impedance

Table 4.2: Restricted diffusion impedance.

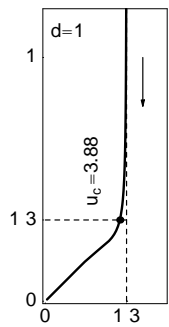
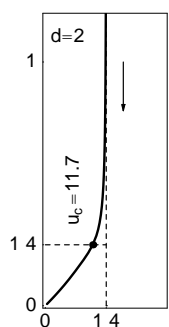
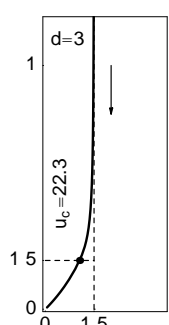
| Denomination | Reduced impedance | Nyquist impedance diagram |
|----------------------------------|--|---|
| Restricted linear diffusion | $Z_{M\delta,1}^* = \frac{\coth \sqrt{i u}}{\sqrt{i u}}$ |  |
| Restricted cylindrical diffusion | $Z_{M\delta,2}^* = \frac{I_0(\sqrt{i u})}{\sqrt{i u} I_1(\sqrt{i u})}$ |  |
| Restricted spherical diffusion | $Z_{M\delta,3}^* = \frac{1}{-1 + \sqrt{i u} \coth \sqrt{i u}}$ |  |

Table 4.3: Restricted diffusion impedance/continued.

| Denomination | Reduced impedance | Nyquist impedance diagram |
|---------------------------------------|--|---------------------------|
| Modified linear restricted diffusion | $Z^* = \frac{\coth(iu)^{\alpha/2}}{(iu)^{\alpha/2}}$ | |
| Anomalous linear restricted diffusion | $Z^* = \frac{\coth(iu)^{\gamma/2}}{(iu)^{1-\gamma/2}}$ | |

Bibliography

- [1] AOKI, K., TOKUDA, K., AND MATSUDA, H. *J. Electroanal. Chem.* 146 (1983), 417.
- [2] AOKI, K., TOKUDA, K., AND MATSUDA, H. *J. Electroanal. Chem.* 160 (1984), 33.
- [3] ARMSTRONG, R. D. *J. Electroanal. Chem.* 198 (1986), 177.
- [4] ARMSTRONG, R. D., BELL, M. F., AND METCALFE, A. A. The A. C. impedance of complex electrochemical reactions. In *Electrochemistry*, vol. 6. The Chemical Society, Burlington House, London, 1978, ch. 3, pp. 98–127.
- [5] BARRAL, G., DIARD, J.-P., AND MONTELLA, C. Étude d'un modèle de réaction électrochimique d'insertion. I-Résolution pour une commande dynamique à petit signal. *Electrochim. Acta* 29 (1984), 239–246.
- [6] BISQUERT, J., AND COMPTE, A. Theory of the electrochemical impedance of anomalous diffusion. *J. Electroanal. Chem.* 499 (2001), 112–120.
- [7] CABANEL, R., BARRAL, G., DIARD, J.-P., B. LE GORREC, AND MONTELLA, C. Determination of the diffusion coefficient of an inserted species by impedance spectroscopy: application to the H/H_xNb₂O₅ system. *J. Appl. Electrochem.* 23 (1993), 93–97.
- [8] CABANEL, R., CHAUSSY, J., MAZUER, J., DELABOUGLISE, G., JOUBERT, J.-C., BARRAL, G., AND MONTELLA, C. Electrochromism of Nb₂O₅ thin films obtained by oxydation of magnetron-sputtered NbN_x. *J. Electrochem. Soc.* 137 (1990), 1444–1451.
- [9] CHEN, J. S., DIARD, J.-P., DURAND, R., AND MONTELLA, C. Hydrogen insertion reaction with restricted diffusion condition. I- Potential step-EIS theory and review for the direct insertion mechanism. *J. Electroanal. Chem.* 406 (1996), 1–13.
- [10] CONTAMIN, O., LEVART, E., MAGNER, C., PARSONS, R., AND SAVY, M. *J. Electroanal. Chem.* 179 (1984), 41.
- [11] CRANK, J. *The Mathematics of Diffusion*, 2 ed. Clarendon Press, Oxford, 1975.
- [12] DESLOUIS, C., GABRIELLI, C., AND TRIBOLLET, B. An analytical solution of the nonsteady convective diffusion equation for rotating electrodes. *J. Electrochem. Soc.* 130, 10 (1983), 2044 – 2046.

- [13] DIARD, J.-P., B. LE GORREC, AND MONTELLA, C. *Cinétique électrochimique*. Hermann, Paris, 1996.
- [14] DROSSBACH, P., AND SCHULTZ, J. *Electrochim. Acta* 11 (1964), 1391.
- [15] GERISCHER, H. *Z. Physik. Chem. (Leipzig)* 198 (1951), 286.
- [16] GORODYSKII, A., MANZHOS, A., AND BABAK, E. On the method for the calculation of Gerischer impedance and its diagnostic criteria. *Electrokhimiya* 18 (2011), 1057.
- [17] HAVRILIAK, S., AND NEGAMI, S. A complex plane analysis of α -dispersions in some polymer systems. *Journal of Polymer Science Part C: Polymer Symposia* 14, 1 (1966), 99 – 117.
- [18] JACOBSEN, T., AND WEST, K. Diffusion impedance in planar cylindrical and spherical symmetry. *Electrochim. Acta* 40 (1995), 255–262.
- [19] KELLER, H. E., AND REINMUTH, W. H. *Anal. Chem.* 44 (1972), 434.
- [20] KUMAR, N. <http://impedance-spectroscopy.blogspot.fr/2014/12/mathematica-test.html>. last visited 10-2-17.
- [21] LASIA, A. Electrochemical Impedance Spectroscopy and its Applications. In *Modern Aspects of Electrochemistry*, vol. 32. Kluwer Academic/Plenum Publishers, 1999, ch. 2, pp. 143 – 248.
- [22] LASIA, A., AND GRÉGOIRE, D. *J. Electrochem. Soc.* 142 (1995), 3393.
- [23] LEVART, E., AND SCHUHMAN, D. Sur la détermination générale de l'impédance de concentration (diffusion convective et réaction chimique) pour une électrode à disque tournant. *J. Electroanal. Chem.* 53 (1974), 77–94.
- [24] LEVILLAIN, E., DEMORTIER, A., AND LELIEUR, J. Electrochemical impedance of solutions of polysulfides in liquid ammonia: experimental evidence for the Gerischer impedance. *J. Electroanal. Chem.* 394, 1-2 (1995), 103 – 115.
- [25] LLOPIS, J., AND COLON, F. In *Proceedings of the Eighth Meeting of the C.I.T.C.E.* (London, 1958), C.I.T.C.E., Butterworths, p. 144.
- [26] LOS, P., RAMI, A., AND LASIA, A. Hydrogen evolution reaction on Ni-Al electrodes. *J. App. Electrochem.* 23 (1993), 135 – 140.
- [27] MACDONALD, J. R. *Impedance spectroscopy. Emphasizing solid materials and systems*. John Wiley & Sons, 1987.
- [28] MAHON, P. J., AND OLDHAM, K. B. Convolutional modelling of electrochemical processes based on the relationship between the current and the surface concentration. *J. Electroanal. Chem.* 464 (1999), 1–13.
- [29] MICHEL, R., AND MONTELLA, C. Diffusion–convection impedance using an efficient analytical approximation of the mass transfer function for a rotating disk. *Journal of Electroanalytical Chemistry* 736 (2015), 139 – 146.

- [30] MOHAMEDI, M., BOUTEILLON, J., AND POIGNET, J.-C. Electrochemical impedance spectroscopy study of indium couples in LiCl-KCl eutectic at 450°C. *Electrochim. Acta* 41 (1996), 1495–1504.
- [31] MONTELLA, C. Review and theoretical analysis of ac-av methods for the investigation of hydrogen insertion. I. Diffusion formalism. *J. Electroanal. Chem.* 462 (1999), 73 – 87.
- [32] MONTELLA, C. EIS study of hydrogen insertion under restricted diffusion conditions. I. Two-step insertion reaction. *J. Electroanal. Chem.* 497 (2001), 3–17.
- [33] MONTELLA, C., DIARD, J.-P., AND B. LE GORREC. *Exercices de cinétique électrochimique. II. Méthode d'impédance*. Hermann, Paris, 2005.
- [34] POTOTSKAYA, V., AND GICHAN, O. On the theory of the generalized Gerischer impedance for an electrode with modeling roughness. *Electrochim. Acta* 235 (2017), 583 – 594.
- [35] RAISTRICK, D., MACDONALD, J. R., AND FRANCESCHETTI, D. R. Impedance spectroscopy. Wiley, New York, 1987, p. 60.
- [36] RAMI, A., AND LASIA, A. Kinetics of hydrogen evolution on Ni-Al alloy electrodes. *J. App. Electrochem.* 22 (1992), 376 – 382.
- [37] RANGLES, J. E. Kinetics of rapid electrode reactions. *Discuss. Faraday Soc.* 1 (1947), 11. 1947, a great year for equivalent circuits, wine (in France) and men (in France).
- [38] ROOT, M. J. Electrochemical impedance of AgO/Zn and HgO/Zn cells. *J. Appl. Electrochem.* 26 (1996), 547–549.
- [39] SANCHEZ, S., CASSAIGNON, S., VEDEL, J., AND MEIER, H. G. Copper diffusion in solid copper sulfide electrode. *Electrochim. Acta.* 41 (1996), 1331 – 1339.
- [40] SCHUHMANN, D. *Compt. rend.* 262 (1966), 1125.
- [41] SLUYTERS, J. H. PhD thesis, Utrecht, 1956.
- [42] SLUYTERS-REHBACH, M. Impedance of electrochemical systems: Terminology, nomenclature and representation-Part I: Cells with metal electrodes and liquid solution (IUPAC Recommendations 1994). *Pure & Appl. Chem.* 66 (1994), 1831–1891.
- [43] SLUYTERS-REHBACH, M., AND SLUYTERS, J. H. Sine wave methods in the study of electrode processes. In *Electroanalytical Chemistry*, A. J. Bard, Ed., vol. 4. Marcel Dekker, Inc., New York, 1970, ch. 1, pp. 1–128.
- [44] SLUYTERS-REHBACH, M., AND SLUYTERS, J. H. In *Comprehensive Treatise of Electrochemistry*, B. C. E. Yeager, J. O'M Bockris and S. S. Eds., Eds., vol. 9. Plenum Press, New York and London, 1984, p. 274.
- [45] VANDERNOOT, T. J. Limitations in the analysis of ac impedance data with poorly separated faradaic and diffusional processes. *J. Electroanal. Chem.* 300 (1991), 199–210.

- [46] WARBURG, E. Uber das Verhalten sogenannter unpolarisierbarer Electroden gegen Wechselstrom. *Ann. Phys. Chem.* 67 (1899), 493–499.
- [47] WOLFRAM, S. *Mathematica Version 3*. Cambridge University Press, 1996.
- [48] YANG, T.-H., AND PYUN, S.-I. *Electrochim. Acta* 41 (1996), 843.
- [49] YZERMANS, A. B. PhD thesis, Utrecht, 1965.